



Pin Diagram

THC63LVD1022

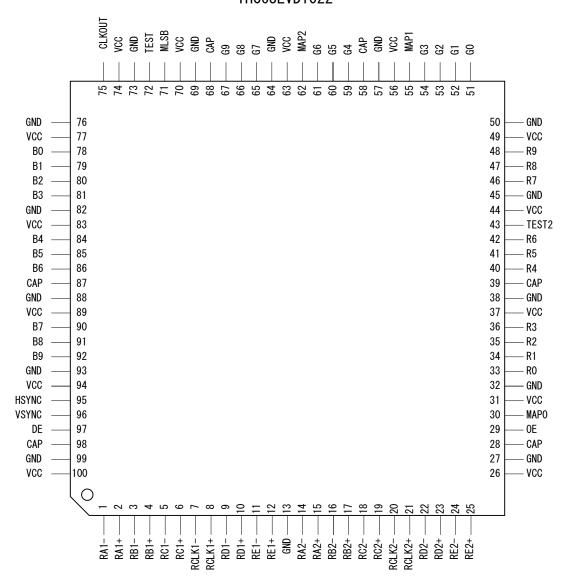


Figure 2. Pin Diagram



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Pin Description

Pin Name	Pin #	Direction	Type			Descrip	tion		
RA1+, RA1-	2, 1								
RB1+, RB1-	4, 3								
RC1+, RC1-	6, 5			LVDS 1	lst Link Data	In.			
RD1+, RD1-	10, 9								
RE1+, RE1-	12, 11								
RCLK1+,RCLK1-	8, 7		LVDS	LVDS (Clock Input for	or 1st Li	nk.		
RA2+, RA2-	15, 14		LVDS						
RB2+, RB2-	17, 16								
RC2+, RC2-	19, 18			LVDS 2	2nd Link Data	a In.			
RD2+, RD2-	23, 22								
RE2+, RE2-	25, 24								
RCLK2+,RCLK2-	21, 20			LVDS (Clock Input for	or 2nd L	ink.		
TEST, TEST2	72, 43			Reserve	ed				
					nal Operation	ı			
				(Table.					
OE	29			Output					
		Input			nal Operation				
					Output signal		he previ	ous logic	value)
MLSB	71			-	bit order sele				
					B = 9 / LSB =				
					B = 0 / LSB =				
MAP2 ~ 0	62, 55, 30			Output	color mappin	g select			•
			LVTTL		MAP0:1:2		RGB		,
					11111 0.11.2	Rch	Gch	Bch	
					HHH	R	G	В	
					HHL	R	В	G	
					HLH	В	R	G	
					HLL	В	G	R	
					LHH	G	R	В	
					LHL	G	В	R	
					LLH	R	G	В	
					LLL	R	G	В	

Table 1. Pin Description



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Pin Description (Continued)

Pin Name	Pin #	Direction	Type	Description	
DE	97			Data Enable Output	
VSYNC	96			Vsync Output	
HSYNC	95			Hsync Output	
R9 ~ 0	48, 47, 46, 42, 41,			Pixel Data Output(Rch)	
	40, 36, 35, 34, 33	Output	LVCMOS	Tixer Data Output(Reff)	
G9 ~ 0	67, 66, 65, 61, 60,	Guiput	LVCMOS	Pixel Data Output(Gch)	
	59, 54, 53, 52, 51			1 Ixel Data Output(Octi)	
B9 ~ 0	92, 91, 90, 86, 85,			Pixel Data Output(Bch)	
	84, 81, 80, 79, 78			Tixei Data Output(Bell)	
CLKOUT	75			Clock Output	
VCC	26, 31, 37, 44, 49,				
	56, 63, 70, 74, 77,			Power Supply Pins	
	83, 89, 94, 100				
GND	13, 27, 32, 38, 45,				
	50, 57, 64, 69, 73,		_	Ground Pins	
	76, 82, 88, 93, 99				
CAP	28, 39, 58, 68, 87,			Decoupling cap.	
	98			External 0.1uF or more capacitance required.	

Table 2. Pin Description



Absolute Maximum Ratings

Parameter	Min	Max	Unit
Supply Voltage (VCC)	-0.3	+4.0	V
LVCMOS/TTL Input Voltage	-0.3	VCC + 0.3	V
LVDS Input Pin	-0.3	VCC + 0.3	V
Junction Temperature	-	+125	°C
Storage Temperature	-55	+125	°C

Table 3. Absolute Maximum Rating

Recommended Operating Conditions

Symbol	Parameter		Min	Тур	Max	Unit
-	All Supply Voltage		3.0	3.3	3.6	V
Ta	Operating Ambient Temperature		0	25	+85	°C
	Cloals Emagnamass	LVDS Input	20	-	75	MHz
-	Clock Frequency	LVCMOS Output	40	-	150	MHZ

Table 4. Recommended Operating Conditions

Equivalent LVDS Input Schematic Diagram

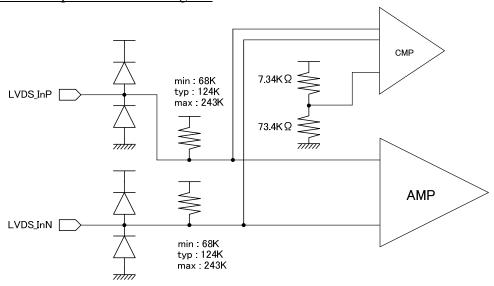
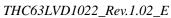


Figure 3. LVDS Input Schematic Diagram

[&]quot;Absolute Maximum Ratings" are those valued beyond which the safety of the device can not be guaranteed. They are not meant to imply that the device should be operated at these limits. The tables of "Electrical Characteristics" specify conditions for device operation.

[&]quot;Absolute Maximum Rating" values also include behavior of overshooting and undershooting.





Power Consumption

Over recommended operating supply and temperature range unless otherwise specified

Symbol	Parameter	Conditions	Typ*	Max	Unit
Ĭ	LVDS Receiver Operating Current Gray Scale Pattern (Fig.4)	RL=100Ω, CL=5pF, RCLK=75MHz	139	ı	mA
I _{RCCW}	LVDS Receiver Operating Current Worst Case Pattern (Fig.5)	RL=100Ω, CL=5pF, RCLK=75MHz	ı	ı	mA

^{*} Typ values are at the conditions of VCC=3.3V and Ta = $+25^{\circ}$ C

Table 5. Power Consumption

Grayscale Pattern

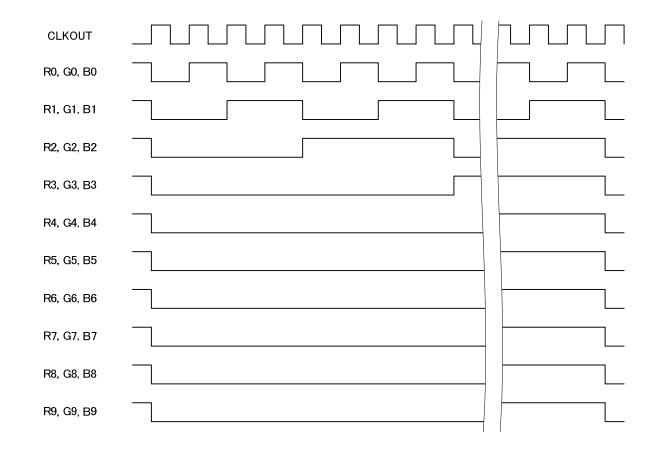


Figure 4. Grayscale Pattern



Worst Case Pattern CLKOUT Rn, Gn, Bn (n = 0~9)

Figure 5. Worst Case Pattern

Electrical Characteristics

DE

HSYNC, VSYNC

LVCMOS/TTL DC Specifications

Over recommended operating supply and temperature range unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ*	Max	Unit
V_{IH}	High Level Input Voltage	RS=VCC or GND	2.0	-	VCC	V
$V_{ m IL}$	Low Level Input Voltage	RS=VCC or GND	GND	-	0.8	V
VOH	High Level Output Voltage	I _{OH} =12mA(Data), 16mA(Clk)	2.4	-	1	V
VOL	Low Level Output Voltage	I _{OH} =12mA(Data), 16mA(Clk)	1	-	0.4	V
I_{IL}	Input Leakage Current		1	-	±1	μΑ
P_{D}	Power Dissipation		-	0.46	-	W

^{*} Typ values are at the conditions of VCC=3.3V and Ta = +25°C

Table 6. LVCMOS/TTL DC Specifications

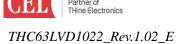
LVDS Receiver DC Specifications

Over recommended operating supply and temperature range unless otherwise specified

		8 FF 3	· · · · · · · · · · · · · · · · · · ·	,		
Symbol	Parameter	Conditions	Min	Typ*	Max	Unit
V_{IC}	Differential Input Common Voltage		0.6	1.2	1.8	V
$ V_{\mathrm{ID} }$	Differential Voltage		100	-	600	mV
V_{TH}	Differential Input High Threshold	$V_{IC} = 1.2V$	-	-	100	mV
V_{TL}	Differential Input Low Threshold	$V_{IC} = 1.2V$	-100	-	-	mV
I _{INLVDS}	LVDS Input Current		-	-	±20	μA

^{*}Typ values are at the conditions of VCC=3.3V and Ta = +25°C

Table 7. LVDS Receiver DC Specifications





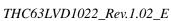
LVCMOS/TTL & LVDS Receiver AC Specifications

Over recommended operating supply and temperature range unless otherwise specified

Symbol	Par	ameter	Min	Тур	Max	Unit	
_	CLK Period	RCLK1/2	13.3	-	50		
t_{RCP}	CLKTCHOU	CLKOUT	6.6	-	25	ns	
t _{RCH}	CLKOUT High Tim	e	2/7 T _{RCP}	4/7 T _{RCP}	5/7 T _{RCP}	ns	
t_{RCL}	CLKOUT Low Time		5/7 T _{RCP}	$3/7 T_{RCP}$	$2/7 T_{RCP}$	ns	
$t_{ m DOUT}$	LVCMOS Data OUT	Γ Period	6.6	-	25	ns	
$t_{ m RS}$	LVCMOS Data Setu	p to CLKOUT	2.0	-	4.6	ns	
t_{RH}	LVCMOS Data Holo	to CLKOUT	2.0	-	4.6	ns	
t_{SK}	Receiver Skew Marg	gin	-400	-	400	ps	
t_{RIP1}	Input Data Position0		- t _{SK}	0	$+$ t_{SK}	ns	
t_{RIP0}	Input Data Position1		$t_{RCIP}/7$ - t_{SK}	$t_{\rm RCIP}/7$	$t_{\text{RCIP}}/7 + t_{\text{SK}}$	ns	
t_{RIP6}	Input Data Position2	•	$2t_{RCIP}/7$ - t_{SK}	$2t_{RCIP}/7$	$2t_{RCIP}/7 + t_{SK}$	ns	
t_{RIP5}	Input Data Position3		$3t_{RCIP}/7$ - t_{SK}	$3t_{RCIP}/7$	$3t_{RCIP}/7 + t_{SK}$	ns	
t_{RIP4}	Input Data Position4		$4t_{RCIP}/7$ - t_{SK}	$4t_{RCIP}/7$	$4t_{RCIP}/7 + t_{SK}$	ns	
t_{RIP3}	Input Data Position5		$5t_{RCIP}/7$ - t_{SK}	$5t_{\rm RCIP}/7$	$5t_{RCIP}/7 + t_{SK}$	ns	
t_{RIP2}	Input Data Position6	·	$6t_{RCIP}/7$ - t_{SK}	$6t_{RCIP}/7$	$6t_{RCIP}/7 + t_{SK}$	ns	
t_{RPLL}	Phase Lock Loop Se	t	-	-	1	ms	

^{*} Typ values are at the conditions of VCC=3.3V and Ta = $+25^{\circ}$ C

Table 8. LVCMOS/TTL & LVDS Receiver AC Specifications





AC Timing Diagrams

LVCMOS Output

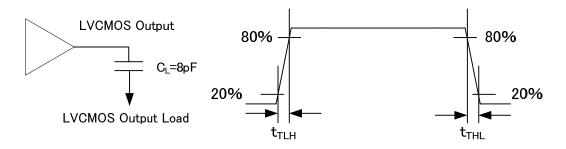


Figure 6. CLKOUT Transmission Time

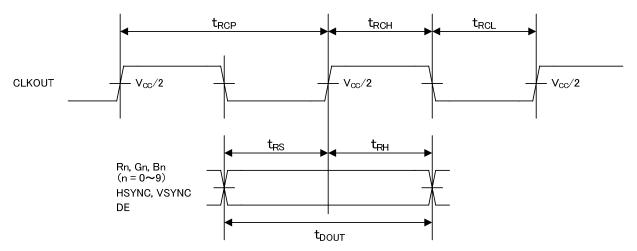
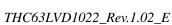


Figure 7. CLKOUT Period, High/Low Time, Setup/Hold Timing





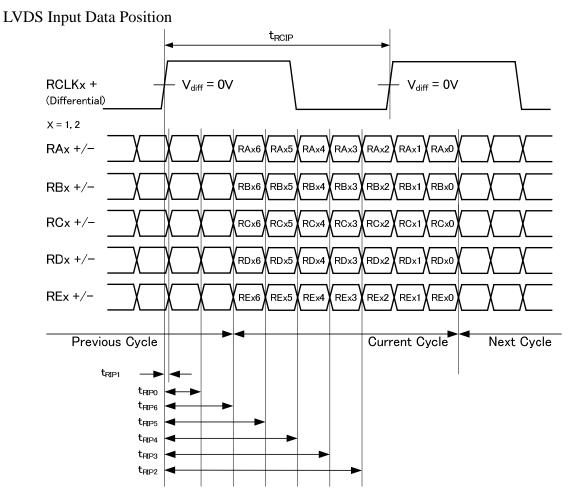


Figure 8. LVDS Input Data Position

Phase Lock Loop Set Time

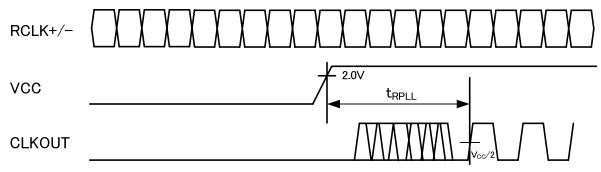


Figure 9. PLL Lock Set Time



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LVDS Data Timing Diagram

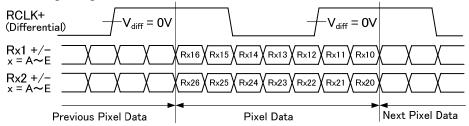
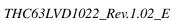


Figure 10. LVDS Data Timing Diagram

LVDS Input Data Mapping (MLSB=High, MAP[2:0]=High)

LVDS Input Data Mapping (MLSB=High, MAP[2:0]=High)				
LVDS		LVDS		
Input Data	1 st pix data	Input Data	2 nd pix data	
(1 st Pixel Data)		(2 nd Pixel Data)		
RA10	R4 (n)	RA20	R4 (n+1)	
RA11	R5 (n)	RA21	R5 (n+1)	
RA12	R6 (n)	RA22	R6 (n+1)	
RA13	R7 (n)	RA23	R7 (n+1)	
RA14	R8 (n)	RA24	R8 (n+1)	
RA15	R9 (n)	RA25	R9 (n+1)	
RA16	G4 (n)	RA26	G4 (n+1)	
RB10	G5 (n)	RB20	G5 (n+1)	
RB11	G6 (n)	RB21	G6 (n+1)	
RB12	G7 (n)	RB22	G7 (n+1)	
RB13	G8 (n)	RB23	G8 (n+1)	
RB14	G9 (n)	RB24	G9 (n+1)	
RB15	B4 (n)	RB25	B4 (n+1)	
RB16	B5 (n)	RB26	B5 (n+1)	
RC10	B6 (n)	RC20	B6 (n+1)	
RC11	B7 (n)	RC21	B7 (n+1)	
RC12	B8 (n)	RC22	B8 (n+1)	
RC13	B9 (n)	RC23	B9 (n+1)	
RC14	HSYNC	RC24	-	
RC15	VSYNC	RC25	-	
RC16	DE	RC26	-	
RD10	R2 (n)	RD20	R2 (n+1)	
RD11	R3 (n)	RD21	R3 (n+1)	
RD12	G2 (n)	RD22	G2 (n+1)	
RD13	G3 (n)	RD23	G3 (n+1)	
RD14	B2 (n)	RD24	B2 (n+1)	
RD15	B3 (n)	RD25	B3 (n+1)	
RD16	-	RD26	-	
RE10	R0 (n)	RE20	R0 (n+1)	
RE11	R1 (n)	RE21	R1 (n+1)	
RE12	G0 (n)	RE22	G0 (n+1)	
RE13	G1 (n)	RE23	G1 (n+1)	
RE14	B0 (n)	RE24	B0 (n+1)	
RE15	B1 (n)	RE25	B1 (n+1)	
RE16	-	RE26	-	

Table 9. LVDS Input Data Mapping





Output Disable Mode

Input Signal	Normal Mode Setting	Output Disable Mode Setting
OE	Н	L
TEST	L	Н
TEST2	L	L
MAP0	X	Н
MAP1	X	Н
MAP2	X	Н
Other Input Signals	X	X

Table 10. Output Disable Mode Setting

Output Signal	Normal Mode	Output Disable Mode
В9	Normal Operation	L
Other Output Signals	Normai Operation	Hi-Z

Table 11. Output Disable Mode Signal Definition





Typical Connection

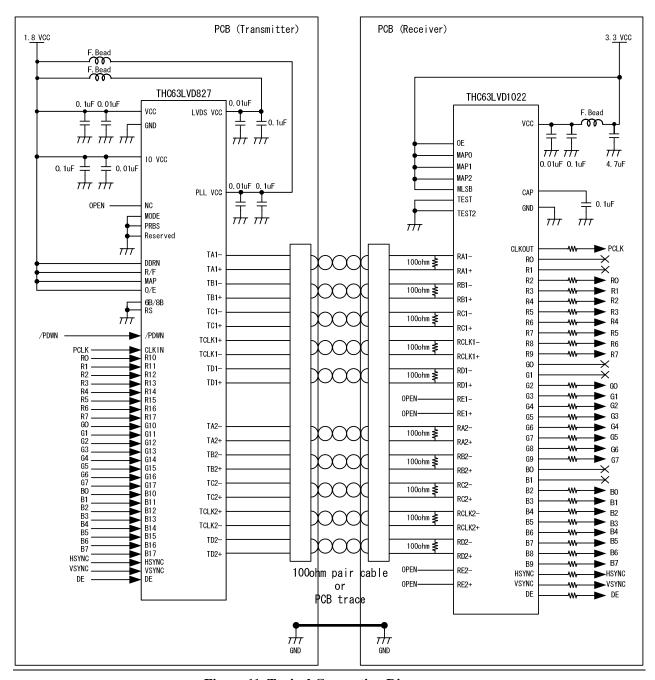


Figure 11. Typical Connection Diagram





Notes

1) Cable Connection and Disconnection

Do not connect and disconnect the LVDS cable, when the power is supplied to the system.

2) GND Connection

Connect each GND of the PCB which THC63LVD1022 and LVDS-Tx on it. It is better for EMI reduction to place GND cable as close to LVDS cable as possible.

3) Multi Drop Connection

Multi drop connection is not recommended.

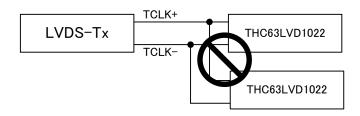


Figure 12. Multi Drop Connection

4) Asynchronous use

Asynchronous using such as following system is not recommended.

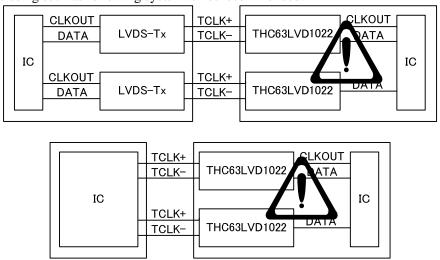
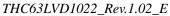


Figure 13. Asynchronous Use





Package

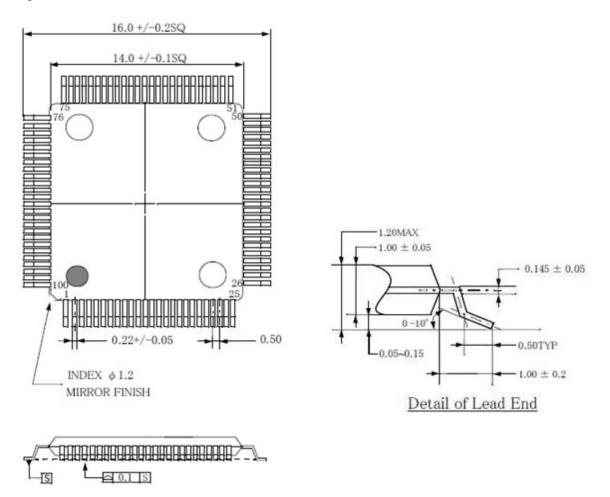
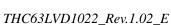


Figure 14. Package Diagram







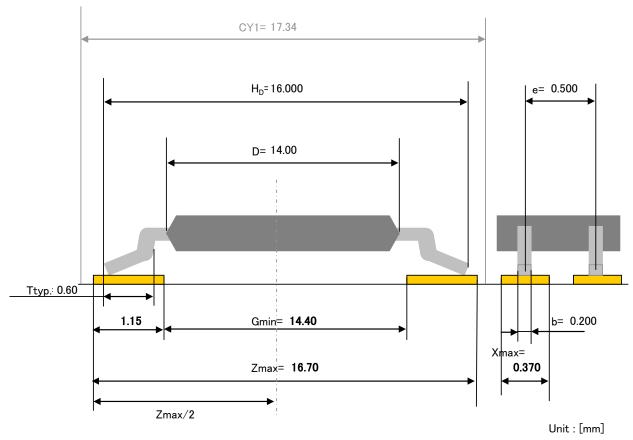


Figure 15. Reference of Land Pattern

The recommendation mounting method of THine device is reflow soldering. The reference pattern is using the calculation result on condition of reflow soldering.

Notes

This land pattern design is a calculated value based on JEITA ET-7501.

Please take into consideration in an actual substrate design about enough the ease of mounting, the intensity of connection, the density of mounting, and the solder paste used, etc... The optimal land pattern size changes with these parameters. Please use the value shown by the land pattern as reference data.



THC63LVD1022 Rev.1.02 E



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